TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74LVX573F,TC74LVX573FT

Octal D-Type Latch with 3-State Output

The TC74LVX573F/FT is a high-speed CMOS octal latch with 3-state output fabricated with silicon gate CMOS technology. Designed for use in 3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

This device is suitable for low-voltage and battery operated systems.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input (\overline{OE}). When the \overline{OE} input is high, the eight outputs are in a high-impedance state.

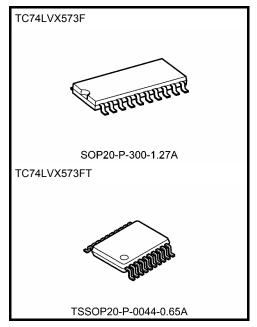
An input protection circuit ensures that 0 to 5.5V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

- High speed: $t_{pd} = 6.4 \text{ ns (typ.) (V}_{CC} = 3.3 \text{ V})$
- Low-power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 \text{°C)}$
- Input voltage level: $V_{IL} = 0.8 \text{ V (max)} (V_{CC} = 3 \text{ V})$

$$V_{IH} = 2.0 \text{ V (min)} (V_{CC} = 3 \text{ V})$$

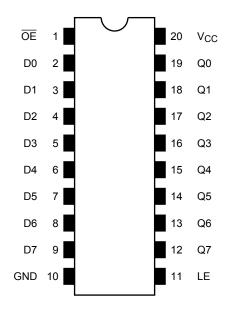
- · Power-down protection provided on all inputs
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74HC573



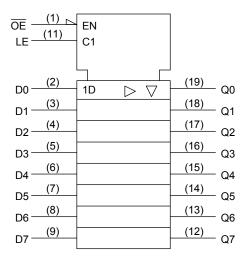
Weight

SOP20-P-300-1.27A : 0.22 g (typ.) TSSOP20-P-0044-0.65A : 0.08 g (typ.)

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

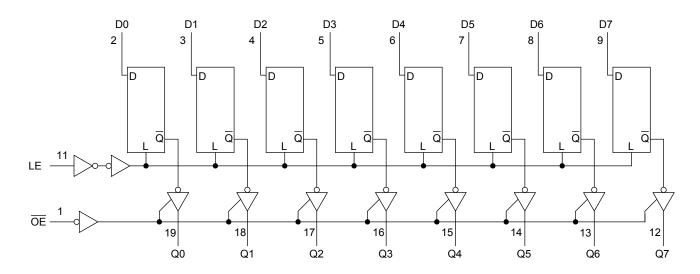
	Inputs	Outputs	
ŌĒ	LE	D	Outputs
Н	Х	Х	Z
L	L	Х	Qn
L	Н	L	L
L	Н	Н	Н

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram



Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to 7.0	V
DC input voltage	V _{IN}	-0.5 to 7.0	V
DC output voltage	V _{OUT}	-0.5 to V_{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage	V _{CC}	2.0 to 3.6	V
Input voltage	V _{IN}	0 to 5.5	٧
Output voltage	V _{OUT}	0 to V _{CC}	٧
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 100	ns/V

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused inputs must be tied to either VCC or GND.

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Electrical Characteristics

DC Characteristics

Characteristics		Sym- bol				Ta = 25°C			Ta = -40 to 85°C		Unit
		DOI			V _{CC} (V)	Min	Тур.	Max	Min	Max	
					2.0	1.5	_	_	1.5	_	
	H-level	V_{IH}		_	3.0	2.0	_	_	2.0	_	
Input voltage					3.6	2.4	_	_	2.4	_	V
input voitage					2.0		_	0.5		0.5	v
	L-level	V_{IL}	_		3.0		_	0.8		0.8	
					3.6 —		_	0.8		0.8	
H-level				$I_{OH} = -50 \mu A$	2.0	1.9	2.0		1.9		
	V _{OH}	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9			
Output voltage				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_		2.48		V
Output Voltage				$I_{OL} = 50 \mu A$	2.0		0	0.1		0.1	V
	L-level	V_{OL}	V _{IN} = V _{IH} or V _{IL}	$I_{OL} = 50 \mu A$	3.0		0	0.1		0.1	
				I _{OL} = 4 mA	3.0		_	0.36		0.44	
3-state output		loz	V _{IN} = V _{IH} or V _{IL}		3.6			±0.25		±2.5	μА
Off-state current		102	$V_{OUT} = V_{CC}$ or GND		3.0			±0.25		±2.5	μΛ
Input leakage curre	nt	I _{IN}	V _{IN} = 5.5 V or GND		3.6	_	_	±0.1	_	±1.0	μΑ
Quiescent supply co	upply current I_{CC} $V_{IN} = V_{CC}$ or GND		3.6	_	_	4.0	_	40.0	μΑ		

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	ool Test Condition		Ta = 25°C	Ta = -40 to 85°C	Unit	
			V _{CC} (V)	Limit	Limit		
Minimum pulse width	to a con		2.7	6.5	7.5	ne	
(LE)	t _{W (H)}	_	3.3 ± 0.3	5.0	5.0	ns	
Minimum set-up time	t _s		2.7	5.0	5.0	200	
		_	3.3 ± 0.3	3.5	3.5	ns	
Minimum hold time	t _h		2.7	1.5	1.5	no	
		_	3.3 ± 0.3	1.5	1.5	ns	



AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Symbol Test Condition				Ta = 25°C			Ta = -40 to 85°C	
			V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	
	+		2.7	15	_	8.2	15.6	1.0	18.5	ns
Propagation delay time	t _{pLH}		2.1	50	_	10.7	19.1	1.0	22.0	
(LE-Q)	+	_	3.3 ± 0.3	15	_	6.4	10.1	1.0	12.0	113
	t _{pHL}		3.3 ± 0.3	50	_	8.9	13.6	1.0	15.5	
	+		2.7	15	_	7.6	14.5	1.0	17.5	
Propagation delay time	t _{pLH}		2.1	50	_	10.1	18.0	1.0	21.0	ns
(D-Q)	.	_	3.3 ± 0.3	15	_	5.9	9.3	1.0	11.0	
, ,	чрНL	t _{pHL}	3.3 ± 0.3	50	_	8.4	12.8	1.0	14.5	
	+		2.7	15	_	7.8	15.0	1.0	18.5	- ns
Outrot analyte time	¹p∠L	t_{pZL} $R_{L} = 1 \text{ k}\Omega$ t_{pZH}	2.1	50	_	10.3	18.5	1.0	22.0	
Output enable time			3.3 ± 0.3	15	_	6.1	9.7	1.0	12.0	
	ιр∠Н		3.3 ± 0.3	50	_	8.6	13.2	1.0	15.5	
Outrout dia alsa tima	t _{pLZ}	$R_L = 1 k\Omega$	2.7	50	_	12.1	19.1	1.0	22.0	20
Output disable time	t_{pHZ}		3.3 ± 0.3	50	_	10.1	13.6	1.0	15.5	ns
Output to output allow	t _{osLH}	(Note 1)	2.7	50	_	_	1.5	_	1.5	ns
Output to output skew	t _{osHL}	(Note 1)	3.3 ± 0.3	50	_	_	1.5	_	1.5	115
Input capacitance	C _{IN}			(Note 2)	_	4	10	_	10	pF
Output capacitance	C _{OUT}		_		_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note 3)	_	29	_	_	_	pF

Note 1: Parameter guaranteed by design.

 $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$

Note 2: Parameter guaranteed by design.

Note 3: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

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Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per latch)}$

And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation:

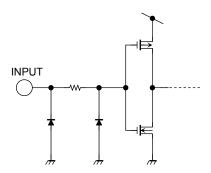
 C_{PD} (total) = 21 + 8 · n



Noise Characteristics (Ta = 25°C, input: $t_r = t_f = 3 \text{ ns}, \, C_L = 50 \text{ pF})$

Characteristics	Symbol	Test Condition	V _{CC} (V)	Тур.	Limit	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	_	3.3	0.5	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	_	3.3	-0.5	-0.8	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V_{IHD}	_	3.3	_	2.0	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}		3.3		0.8	V

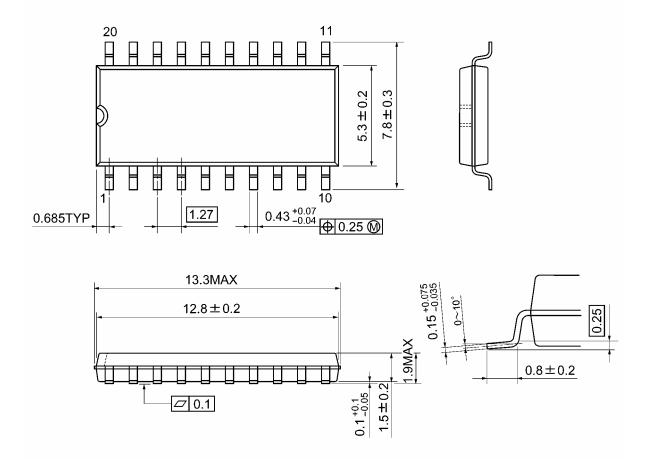
Input Equivalent Circuit



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Package Dimensions

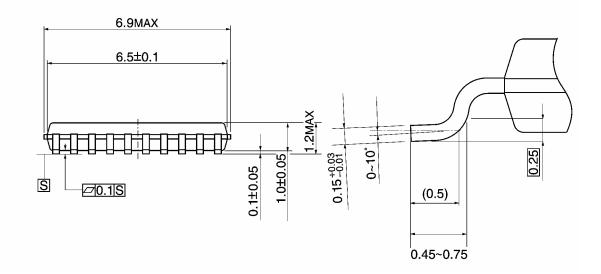
SOP20-P-300-1.27A Unit: mm



Weight: 0.22 g (typ.)

Package Dimensions

TSSOP20-P-0044-0.65A Unit: mm 6.4 ± 0.2 $0.22\substack{+0.09 \\ -0.06}$ 0.65 0.325TYP



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| |0.13M

Weight: 0.08 g (typ.)

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